

PATENT ABSTRACTS OF JAPAN

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(54) PLASMA PROCESSING APPARATUS AND ITS ASSEMBLING METHOD

(57)Abstract:

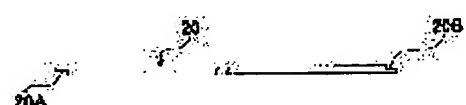
PROBLEM TO BE SOLVED: To overcome the problem of a prior art such that plasma processing is affected adversely when the surface of a shield member 9 is cut off partially by plasma and the surface treatment film is eliminated and, since a decision is made that the life of the shield member 9 has expired even when a limited part thereof is cut off, the shield member 9 must be replaced and a high cost is imposed for replacing the shield member 9.

SOLUTION: The plasma processing apparatus 10 comprises a lower electrode 12 for supporting a wafer W in a chamber 11, a member 19 for shielding the inner circumferential surface of the chamber 11 from plasma for processing the wafer W supported by the lower electrode 12, and a baffle plate 18 disposed in a gap between the shielding member 19 and the lower electrode 12 in order to discharge gas in the chamber 11 while diffusing, wherein a resin plate 20 is fixed replaceably to the inner circumferential surface of the shielding member 19, and the resin plate 20 is imparted with a compressive stress in the circumferential direction.

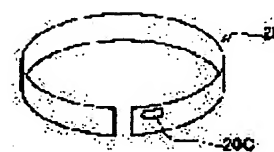
(a)



(b)



(c)



(d)

